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(12) (A)

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2004 11 26
(86) PCT/JP2004/003576 (87) WO 2004/088398
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(30) JP - P - 2003 - 00092267 2003 03 28 (JP)
(71) 4 1-8 ,
(72) , 가 가 1 19-16 301
(74)

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(54)

(6), (7) (10)
(24R) (6) ,
(26) (10) , (6) (7) (24R) (26a) .
(e) ,

, , ,

, .

(R), (G), (B) 가

가 가 가

가

2002-49057

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가

가

- 1
- 2 1
- 3 1
- 4 4
- 5 4 V-V

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1 3 (2) (1) (3)

(1) , (4) , (11) (11)
 (5) (21b), (15a) n-ch LDD(Lightly Doped Drain) TFT(, n-chTFT : 20)가
 n-chTFT(20) , (a-Si) (p-Si) / (1
 2a, 12b) (12) , (15a) (13) p-Si (15b) (11)
 (12) (16) (15a)
 (31)가
 (4) , (11) , (12) , (13) ,
 (14) (15a), (15b), (16) (16) (16)
 (13) (14) (14) (15a), (15b), (16)
 (14) (17)
 (17) , (21a), (21b) (21a) , (21b)
 (12) / (12a), (26) (21b)
 (12) / (12b)
 (21a), (21b), (17) (22) ,
 (24G), (24R), (24B)
 (24G, 24R, 24B)
 (24G, 24R, 24B) , ITO() (26)
 (26) , (22) (25) (21a) (16)
 (26) (21b) (26) (13)
 (BM)
 (24R, 24G) , (27)가
 (27) (24G, 24R, 24B) (26) ,
 (28)
 (5) , (11) Nch LDD TFT(, n-chTFT
) Pch TFT(, p-chTFT) 가
 가
 (5) (1) , (5) (24R) , (4) 가 (27)가
 24R)
 (2) , (51) (51) , ITO
 (52), (53)
 (1) (2) , (27) (1) (2) ,
 (60) (60) (61)가 (62)
 (3) (1) (2)
 (10) , (1) : 10 4 4 (1) , (7)
 (6) , (4) (5) 4 (1)

2 3 , a-Si , XeCl (10) , CVD a-Si , p-Si , p-Si (13)

(4) n-chTFT(20) p-Si , p-chTFT p-Si (10)

(14) SiO_x , CVD , (14) Ta, Cr, Al, Mo, W, Cu (15a), (15b), (16)

n-chTFT p-chTFT

hTFT , p-Si , n-chTFT(20) / n-chTFT(20) p-Si , n-c (12)

) , n-chTFT / (12a, 12b)

FT , (12), n-chTFT p-chTFT / p-chT

n-chTFT LDD (10)

CVD (PE-CVD) (10) (17)

(12) / (12a, 12b) (16)

(17) Ta, Cr, Al, MO, W, Cu (12) / (12b) (21b),

(12a), (26) (21a), (22) (10)

PE-CVD (21a) (23)

(10) (10)

(10) (10)

(21a) (25)

(25) (24G) (24G) 가

(24R) (24B) (4) 5

(24R) (5), (10) (7) (24R)

ITO (26) (7) (24R) (4) (26a)

(21a) (4) (26) (25)

(6) (5) (5) (24R)

(7) (26a) (6) e w (24R)

(6) (7) (10)

(6) (7) (24G, 24R, 24B) (10)

(27) (4) (28) (28) ()

(1) (6) (10) 4

(52) (2) (51) (51) , ITO (51) (52) (53) (2) (2) (10) 1, 2, 5 (6) (2) (60) (2) (10) (6) (10) (6) e (10) (6) e (10) 4 (1) 가 (60) (61) (61) (6) 2) (chiral) 가 가 (1) (2) (3) 가 (1) (2) (7) (24R) (26a) (6) (10) (6) (7) (24R) (10) 24R) (7) (26a) (6) e w (10) (10) (26a) (26a) (4) (26)) (10) (5) (7) (1) 4 (24R) , 3 5 (24G, 24B) (10)

가

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2 3.

1 4. 3

4 5.

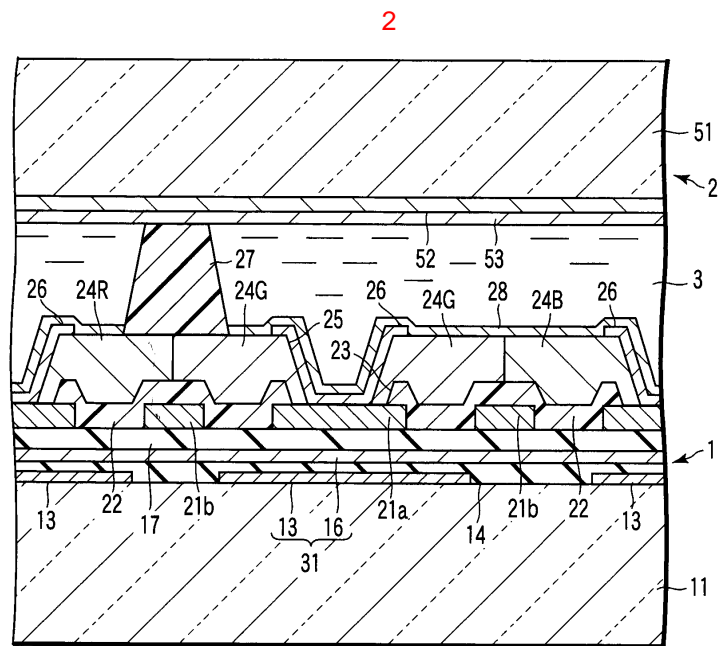
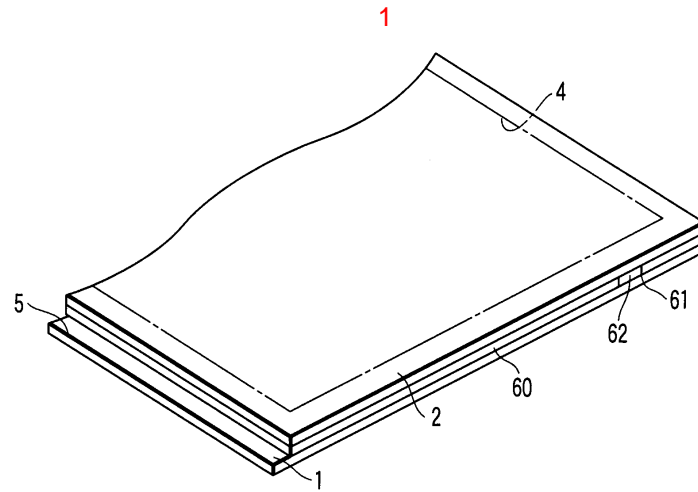
1 6.

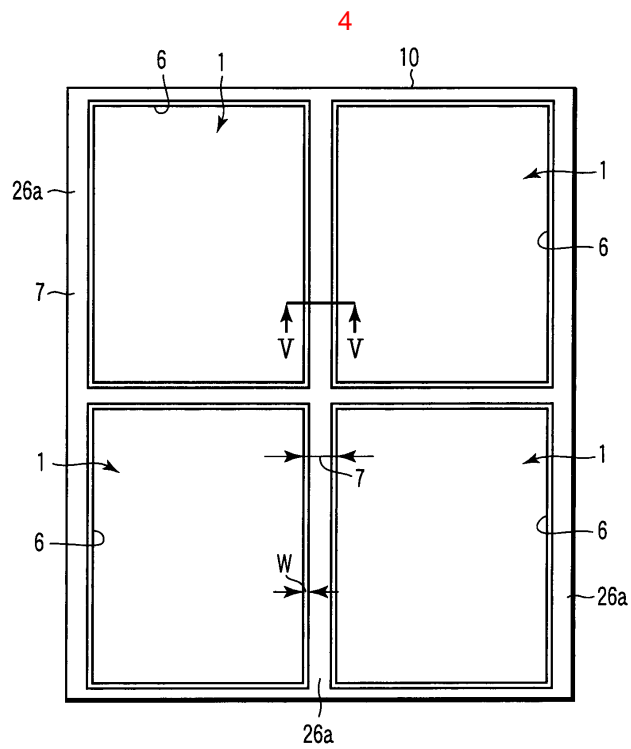
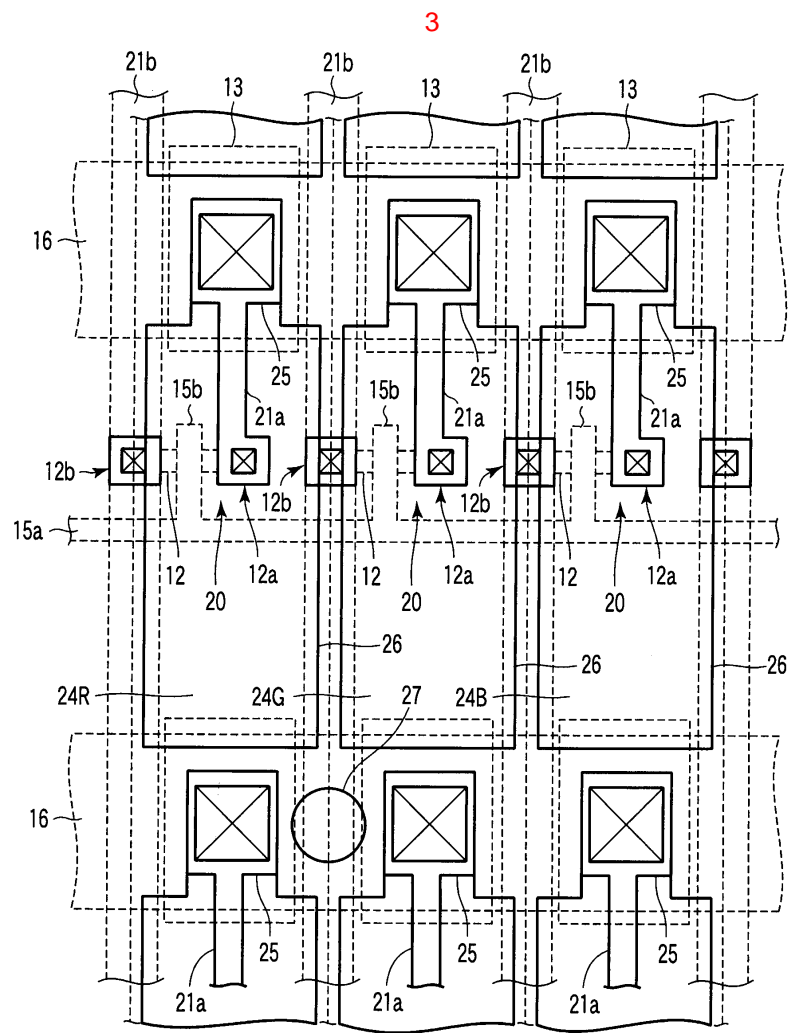
2 7.

3 8.

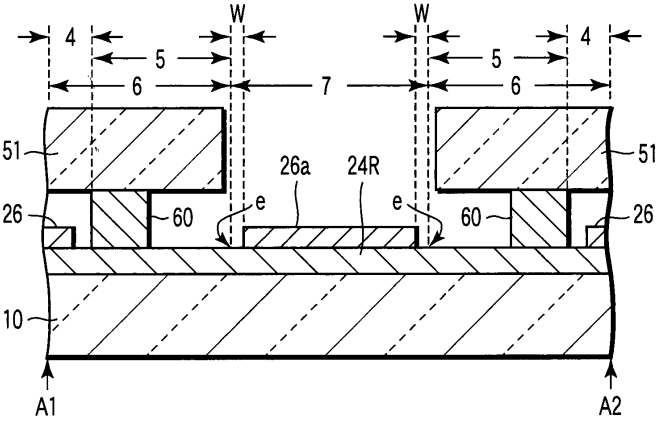
4 9.

5 10.





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专利名称(译)	液晶显示装置的制造方法		
公开(公告)号	KR1020050004236A	公开(公告)日	2005-01-12
申请号	KR1020047019141	申请日	2004-03-17
申请(专利权)人(译)	可否让我这个小粉丝展示中心		
当前申请(专利权)人(译)	可否让我这个小粉丝展示中心		
[标]发明人	MORIYAMA NAOMI		
发明人	MORIYAMA,NAOMI		
IPC分类号	G02F1/1335 G02F1/1339 G02F1/1333 G02F1/1337 G02F1/13 G02F1/1343		
CPC分类号	G02F1/13351		
代理人(译)	LEE , JUNG HEE CHANG, SOO KIL		
优先权	2003092267 2003-03-28 JP		
外部链接	Espacenet		

摘要(译)

准备包括包括阵列面板的可用区域 (6) 和位于可用区域外部的无效区域 (7) 的基板 (10)。彩色层 (24R) 形成在可用区域和无效区域上。它在可用区域 (6) 的彩色层之后重叠并形成导电膜。形成多个像素电极 (26)，它在无效区域 (7) 的彩色层 (24R) 之后重叠，同时形成导电膜 (26a)。其中形成导电膜的基板 (10) 沿可用区域 (6) 的周边部分 (e) 分开。阵列面板被切掉了。可用区域，无效区域，彩色层，导电膜。

